

EAST - [3615.wsp:1] File View Edit Tools Window Help

Active

- L1: (3796) (opening trench via hole recess) with ((plasma gas) near (h2 hydrogen))
- L2: (78) 1 and (opening trench via hole recess) with ((plasma gas) near (chlorine))
- L6: (2) 5 and (opening trench via hole recess) with (silicide)
- L5: (18) 2 and (opening trench via hole recess) with (insulat\$3 dielectric)

Failed

Search  Browse  Clear

Dbs: USPTO; EUB; USPAT; EPO; JPO Default operator: OR  Datab  Highlight all items initially

2 and (opening trench via hole recess) with (insulat\$3 dielectric)

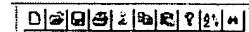
44 ERS Form

U	I	Document I	Issue Date	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
1	<input checked="" type="checkbox"/>	US 2005021	2005003757.7		Method of fabricating semiconductor device.	438/270			Nunizawa, Sumito et.al.	<input checked="" type="checkbox"/>					
2	<input checked="" type="checkbox"/>	US 2004082	2004016665.6		METHOD OF FABRICATING SEMIC	438/589	257/E21.4	19:	Nunizawa, Sumito et.al.	<input checked="" type="checkbox"/>					
3	<input checked="" type="checkbox"/>	US 2003070	2003012480.3		Method of fabricating semiconductor device.	438/270	257/E21.4	19:	Nunizawa, Sumito et.al.	<input checked="" type="checkbox"/>					
4	<input checked="" type="checkbox"/>	US 20030111	2003001331.6	23	Process for fabricating semiconductor device.	438/706	257/E21.2	52:	Negishi, Nobuyuki et.al.	<input checked="" type="checkbox"/>					
5	<input checked="" type="checkbox"/>	US 2002072	2002009865.5		Method of fabricating semiconductor device.	438/270	257/E21.4	19:	Nunizawa, Sumito et.al.	<input checked="" type="checkbox"/>					
6	<input checked="" type="checkbox"/>	US 2002012	2002000986.4		Method of fabricating semiconductor device.	438/589	257/288;	257/330:	Nunizawa, Sumito et.al.	<input checked="" type="checkbox"/>					
7	<input checked="" type="checkbox"/>	US 6803281	2004101	B2	Method of fabricating semiconductor device.	438/270	257/288;	257/328:	Nunizawa, Sumito et.al.	<input checked="" type="checkbox"/>					
8	<input checked="" type="checkbox"/>	US 6720220	2004041	B2	Method of fabricating semiconductor device.	438/270	257/288;	257/328:	Nunizawa, Sumito et.al.	<input checked="" type="checkbox"/>					
9	<input checked="" type="checkbox"/>	US 6645870	2003111	21	Process for fabricating semiconductor device.	438/710	257/E21.2	52:	Negishi; Nobuyuki et.al.	<input checked="" type="checkbox"/>					
10	<input checked="" type="checkbox"/>	US 6512265	2003012	B2	Method of fabricating semiconductor device.	257/330	257/288;	257/328:	Nunizawa; Sumito et.al.	<input checked="" type="checkbox"/>					
11	<input checked="" type="checkbox"/>	US 6410959	2002062	B2	Method of fabricating semiconductor device.	257/330	257/341;	257/342:	Nunizawa; Sumito et.al.	<input checked="" type="checkbox"/>					
12	<input checked="" type="checkbox"/>	US 6307231	2001102	B1	Method of fabricating semiconductor device.	257/330	257/341;	257/342:	Nunizawa; Sumito et.al.	<input checked="" type="checkbox"/>					

Help  Details  HTML

Ready

NUM



e-- Active

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e-- Failed

Search	Loc	Browse	Print	Exit
DBs:	US-PG+UB:USPAT:EPG,JPO	<input checked="" type="checkbox"/> Bulk <input type="checkbox"/> Highlight all items initially		
Default operator: OR				
2 and (opening trench via hole recess) with (insulator\$3 dielectric)				
<input type="button" value="ERForm"/> <input type="button" value="ISARform"/> <input type="button" value="Image"/> <input type="button" value="Text"/> <input type="button" value="HTML"/>				

U	I	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	4
7	✓	US 6803281	2004101		Method of fabricating semiconductor device	438/270	257/288; 257/328;		Numazawa; Sumito et.al.	✓	✓	✓	✓	✓	✓
8	✓	US 6720220	2004041		Method of fabricating semiconductor device	438/270	257/288; 257/328;		Numazawa; Sumito et.al.	✓	✓	✓	✓	✓	✓
9	✓	US 6645870	2003111	21	Process for fabricating semiconductor device	438/710	257/E21.2 52;		Negishi; Nobuyuki et.al.	✓	✓	✓	✓	✓	✓
10	✓	US 6512265	2003012		Method of fabricating semiconductor device	257/330	257/288; 257/328;		Numazawa; Sumito et.al.	✓	✓	✓	✓	✓	✓
11	✓	US 6410959	2002062		Method of fabricating semiconductor device	257/330	257/341; 257/342;		Numazawa; Sumito et.al.	✓	✓	✓	✓	✓	✓
12	✓	US 6307231	2001102		Method of fabricating semiconductor device	257/330	257/341; 257/342;		Numazawa; Sumito et.al.	✓	✓	✓	✓	✓	✓
13	✓	US 6168996	2001010		Method of fabricating semiconductor device	438/270	257/330; 257/E21.4		Numazawa; Sumito et.al.	✓	✓	✓	✓	✓	✓
14	✓	US 5458858	1995101		Integrated procedure for high yield production of	422/234	422/129; 422/200;		Dawkins; John L.	✓	✓	✓	✓	✓	✓
15	✓	US 5324497	1994062		Integrated procedure for high yield production of	423/478	204/277; 204/278;		Westerlund; G. Oscar	✓	✓	✓	✓	✓	✓
16	✓	US 4935800	1990061		Semiconductor integrated circuit	257/520	257/378; 257/501;		Taguchi; Minoru	✓	✓	✓	✓	✓	✓
17	✓	JP 20011051	2001126989.1		METHOD OF FORMING SEMICOND				ODA, KATSUYA	✓	✓	✓	✓	✓	✓
18	✓	JP 1992101	04286115.A.2		MANUFACTURE OF SEMICONDUCTOR DE		438/701; 438/714;		SHIOTANI, YOSHIMI et.al.	✓	✓	✓	✓	✓	✓